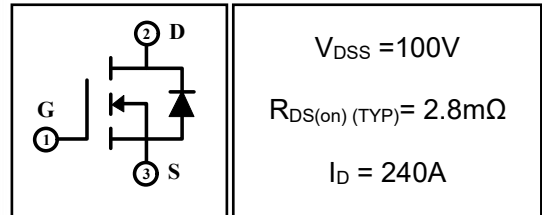


240A 100V N-channel Enhancement Mode Power MOSFET

1 Description

The N-channel enhancement mode power mosfets used advanced split gate trench technology design, provided excellent $R_{DS(on)}$ and low gate charge. Which accords with the RoHS standard.

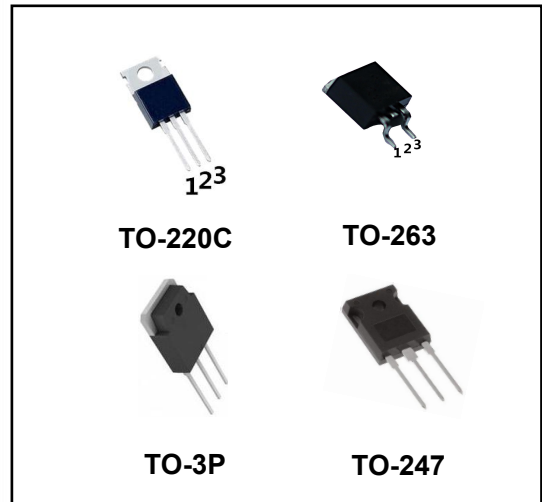


2 Features

- Low on resistance
- Low gate charge
- Fast switching
- Low reverse transfer capacitances
- High avalanche current
- 100% single pulse avalanche energy test
- 100% ΔV_{DS} test

3 Applications

- Inverter management system
- Power tools
- UPS(Uninterruptible Power Supplies)
- Motor control
- Battery management



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

Parameter	Symbol	Rating			Units
		DHS025N10	DHS025N10E	DHS025N10D DHS025N10B	
Drain-to-Source Voltage	V_{DSS}	100			V
Gate-to-Source Voltage	V_{GSS}	±20			V
Continuous Drain Current (Silicon Limited)	$T_C=25^\circ C$	352			A
	$T_C=100^\circ C$	281			A
Drain Current(continuous) ⁽³⁾ (Package Limited) $T_C=25^\circ C$	I_D	240			A
Pulsed Drain Current ⁽¹⁾	I_{DM}	960			A
Single Pulse Avalanche Energy ⁽⁴⁾	E_{AS}	1877			mJ
Avalanche Current ⁽⁴⁾	I_{AS}	87			A
Power Dissipation	$T_a=25^\circ C$	2	2	3	W
	$T_C=25^\circ C$	356	356	356	W
Junction Temperature Range	T_j	-55 ~ 175			°C
Storage Temperature Range	T_{stg}	-55 ~ 175			°C

4.2 Thermal Characteristics

Parameter	Symbol	Rating			Units
		DHS025N10	DHS025N10E	DHS025N10D DHS025N10B	
Thermal Resistance, Junction to Case-sink	R_{thJC}	0.421	0.421	0.421	°C/W
Thermal Resistance, Junction to Ambient	R_{thJA}	75	75	50	°C/W

4.2 Electrical Characteristics (Tc=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Units
			Min	Typ	Max	
Off Characteristics						
Drain-to-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	100	116	—	V
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V, T _C =25°C	—	—	1	μA
		V _{DS} =100V, V _{GS} =0V, T _C =125	—	—	100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	—	—	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-to-Source on-state Resistance	R _{DS(on)}	V _{GS} =10V, I _D =80A	—	2.8	3.6	mΩ
Forward Transfer Conductance	g _{fs}	V _{DS} =5V, I _D =80A	—	177	—	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =50V, f=1.0MHz	—	14475	—	pF
Output Capacitance	C _{oss}		—	1280	—	
Reverse Transfer Capacitance	C _{rss}		—	50	—	
Gate Resisitance	R _G	V _{DD} =0V, V _{GS} =0V, F=1MHz	—	3.0	—	Ω
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	I _D =80A, V _{DS} =50V, V _{GS} =10V, R _R =1.6Ω	—	33.3	—	nS
Turn-on Rise Time	t _r		—	114	—	
Turn-off Delay Time	t _{d(off)}		—	101	—	
Turn-off Fall Time	t _f		—	98.3	—	
Total Gate Charge	Q _g	I _D =80A, V _{DS} =50V, V _{GS} =10V,	—	204.6	—	nC
Gate-to-Source Charge	Q _{gs}		—	79.5	—	
Gate-to-Drain("Miller") Charge	Q _{gd}		—	37.3	—	
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽³⁾	V _{SD}	V _{GS} =0V, I _S =60A	—	—	1.2	V
Diode Forward Current	I _S		—	—	180	A
Reverse Recovery Time ⁽³⁾	t _{rr}	T _J =25°C, I _F =100A, dI _F /dt=100A/μS, V _{GS} =0V	—	68	—	nS
Reverse Recovery	Q _{rr}		—	56	—	nC

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, t_l≤10sec.
- 3: Pulse width ≤ 300μs, duty cycle ≤ 2%.
- 4: L=0.5mH, I_D=87A, V_{DD}=100V, V_{GATE}=100V, Start T_J=25°C.

5 Typical characteristics diagrams

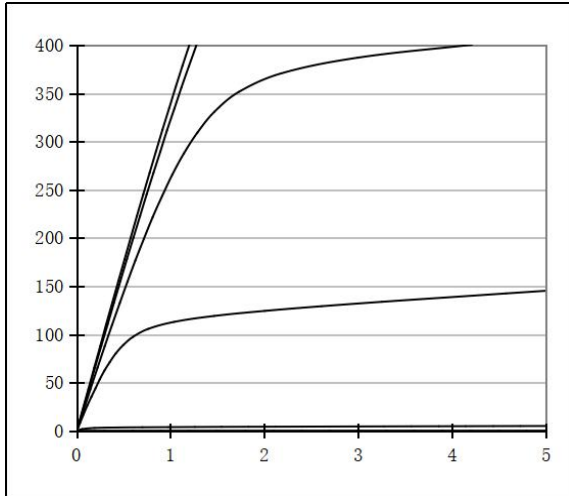


Fig 1. Output Characteristics

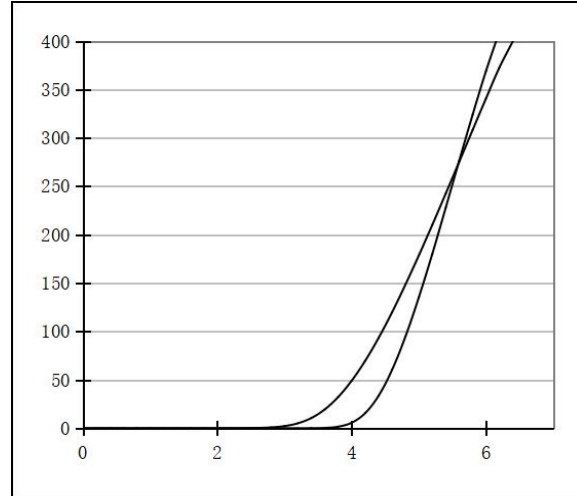


Fig 2. Transfer Characteristics

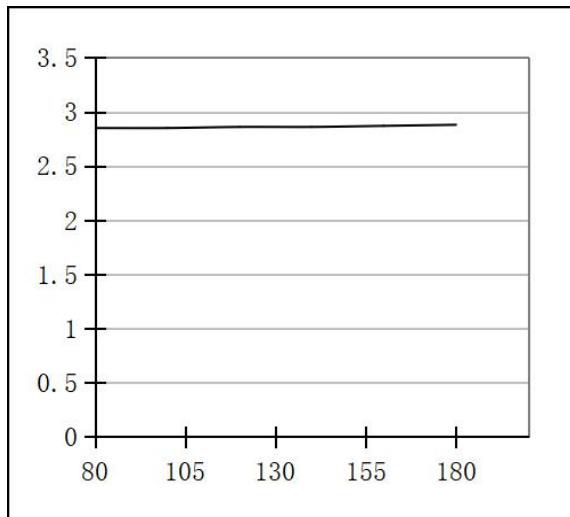


Fig 3. Rdson-Drain Current

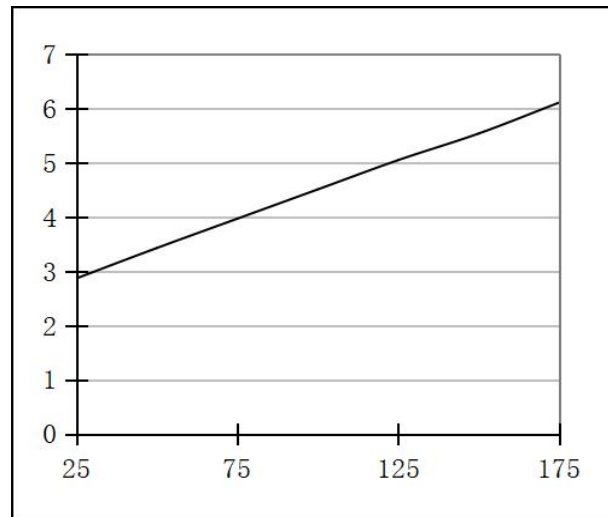


Fig 4. Rdson-Junction Temperature

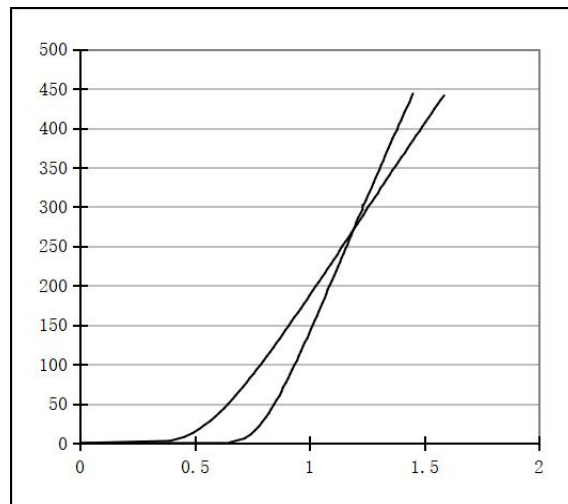


Fig 5. Source-Drain Diode Forward

5 Typical characteristics diagrams(Continues)

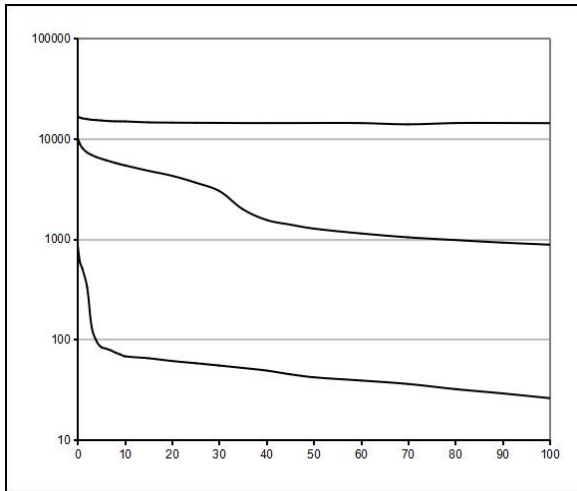


Fig 6. Capacitance vs Vds

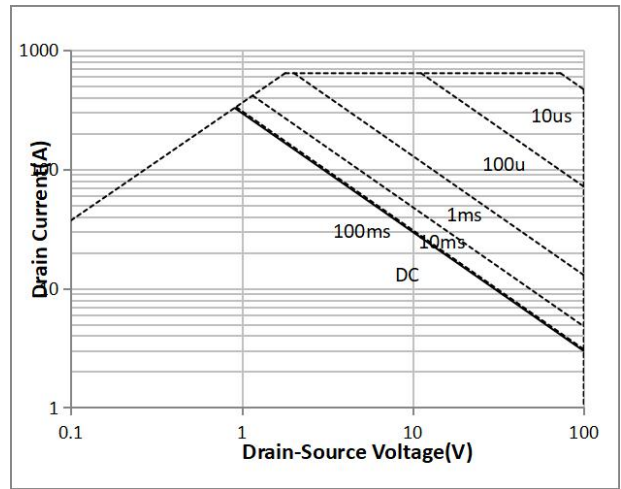


Fig 7. Safe Operation Area

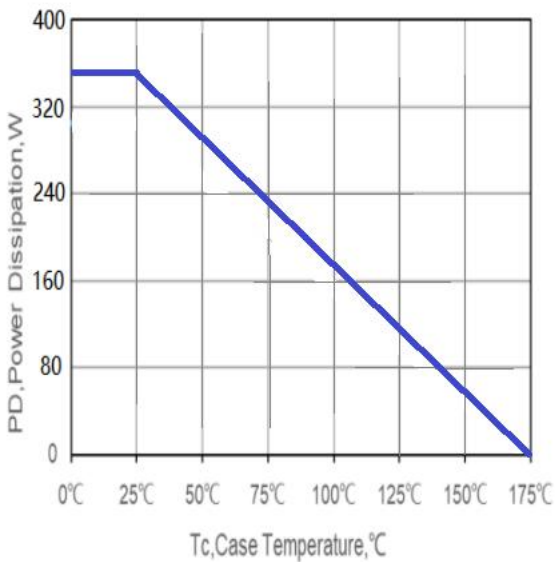


Fig 8. Power De-rating

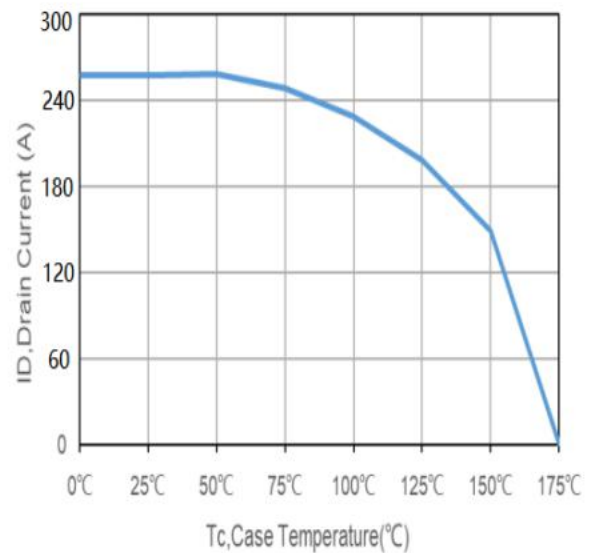


Fig 9. Current De-rating

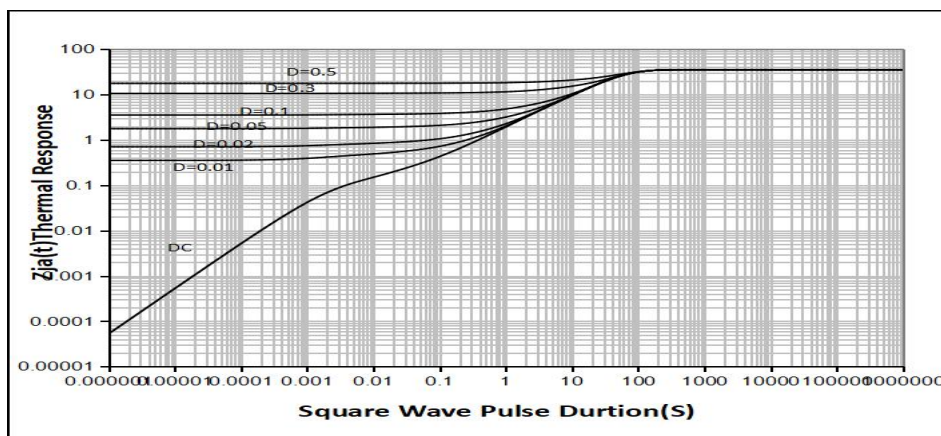
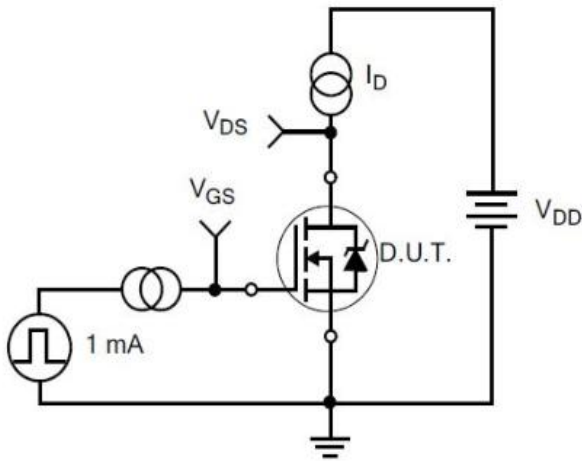
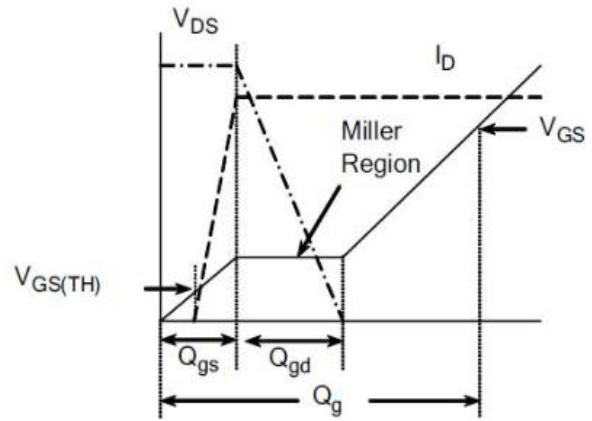


Fig 10. Normalized Maximum Transient Thermal Impedance

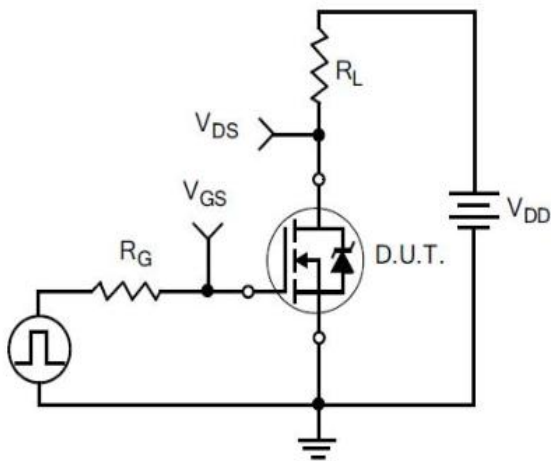
6 Typical Test Circuit and Waveform



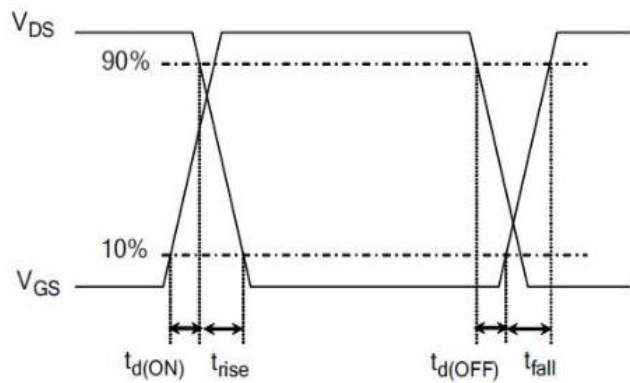
1) Gate Charge Test Circuit



2) Gate Charge Waveform

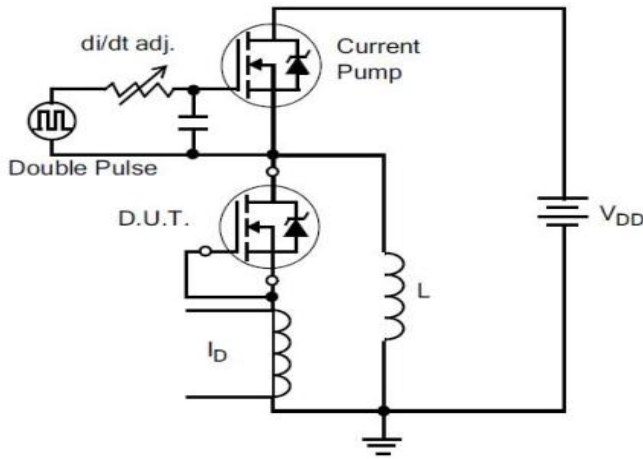


3) Resistive Switching Test Circuit

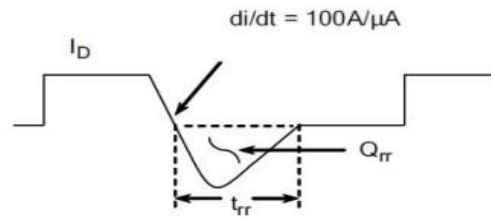


4) Resistive Switching Waveforms

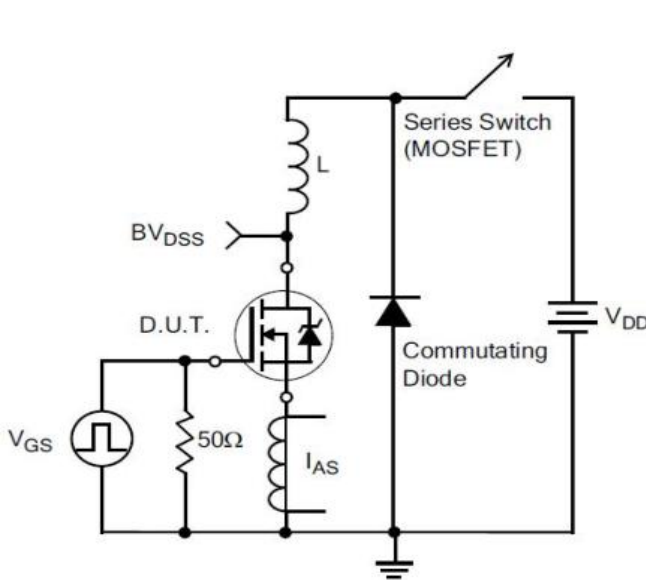
6 Typical Test Circuit and Waveform(continues)



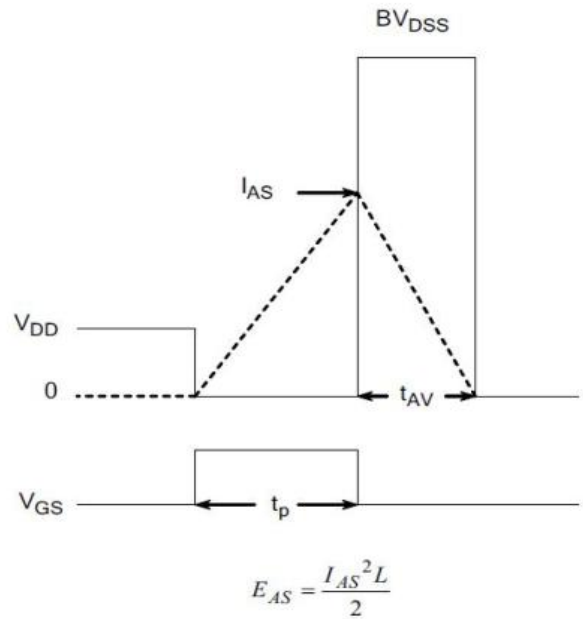
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

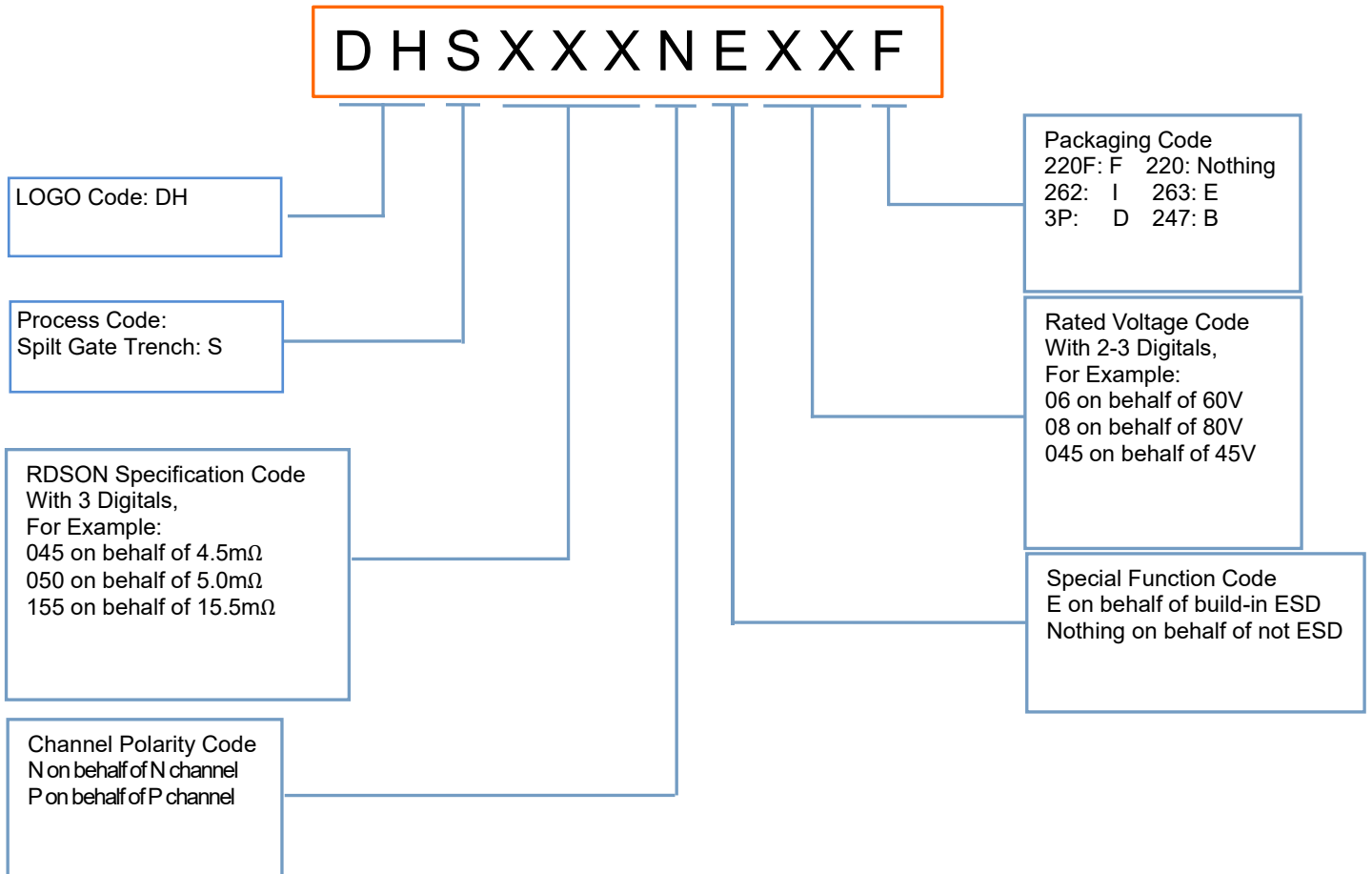


7) . Unclamped Inductive Switching Test Circuit



8) Unclamped Inductive Switching Waveforms

7 Product Names Rules

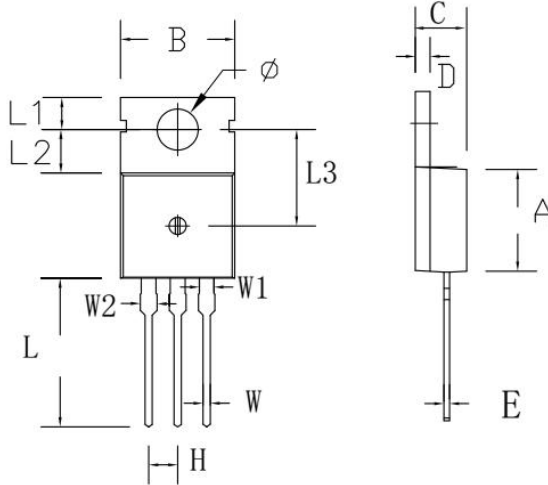


8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
DHS025N10	TO-220	DHS025N10	Pb-free	Tube	1000/box
DHS025N10E	TO-263	DHS025N10E	Pb-free	Tape & Reel	800/box
DHS025N10D	TO-3P	DHS025N10D	Pb-free	Tube	300/box
DHS025N10B	TO-247	DHS025N10B	Pb-free	Tube	300/box

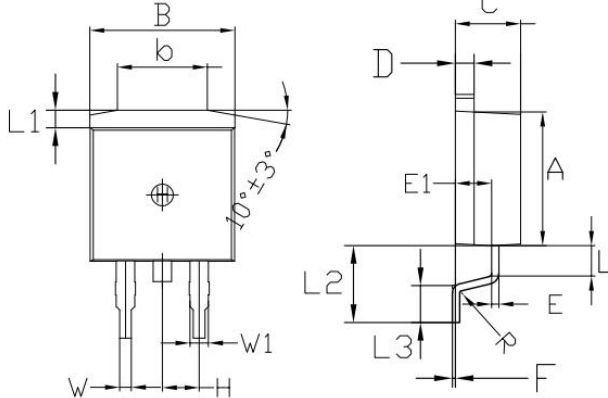
9 Dimensions

TO-220C PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
H	2.54 TYP		0.100 TYP	
W	0.60	0.95	0.024	0.037
W1	1.05	1.45	0.041	0.057
W2	1.20	1.60	0.047	0.063
L	12.60	13.40	0.496	0.528
L1	2.45	2.95	0.096	0.116
L2	3.45	3.95	0.136	0.156
L3	8.15	8.65	0.321	0.341
Φ	3.50	3.90	0.138	0.154

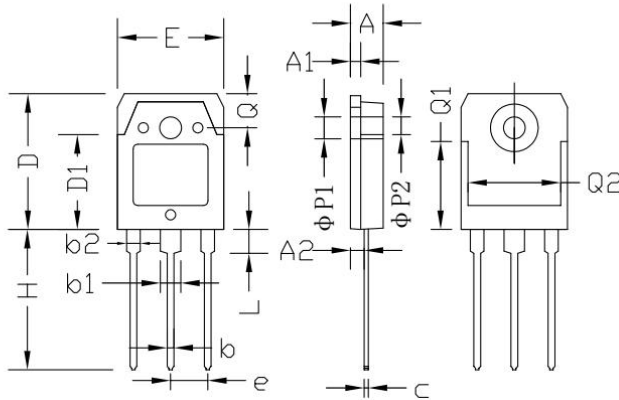
TO-263 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	9.70	10.30	0.382	0.406
C	4.25	4.75	0.167	0.187
D	1.20	1.45	0.047	0.057
E	0.40	0.60	0.016	0.024
L	1.90	2.30	0.075	0.091
L1	1.15	1.45	0.045	0.057
R	0.24	0.26	0.0095	0.0102
W	0.80	0.82	0.0315	0.0323
W1	1.20	1.30	0.047	0.051
H	2.54 TYP		0.200 TYP	
b	5.50	6.50	0.216	0.256
E1	2.4	2.6	0.0946	0.1024
L2	5.20	5.80	0.205	0.228
L3	2.20	3.20	0.087	0.126
F	0.03	0.23	0.0012	0.0091

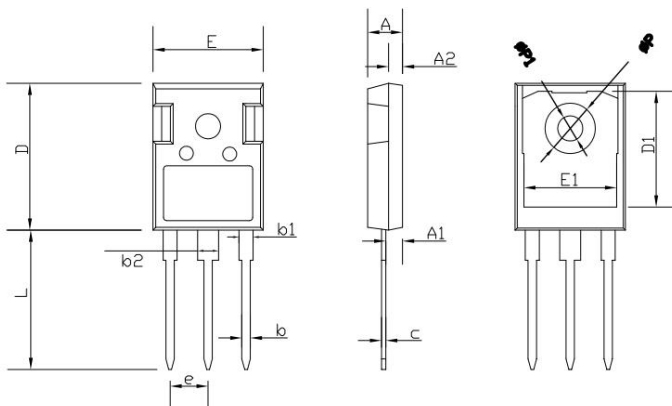
9 Dimensions(continues)

TO-3PN PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	4.60	5.00	0.181	0.197
A1	1.45	1.65	0.057	0.065
A2	2.20	2.60	0.087	0.102
b	0.80	1.20	0.032	0.047
b1	2.80	3.20	0.110	0.126
b2	1.80	2.20	0.071	0.087
C	0.55	0.75	0.022	0.030
D	19.20	19.70	0.756	0.776
D1	13.10	14.70	0.516	0.578
E	15.40	15.80	0.607	0.623
e	5.45 TYP		0.215 TYP	
H	19.80	20.20	0.780	0.826
L	3.30	3.70	0.130	0.146
ΦP1	3.20 TYP		0.126 TYP	
ΦP2	3.50 TYP		0.138 TYP	
Q	5.00 TYP		0.197 TYP	
Q1	12.40 TYP		0.488 TYP	
Q2	12.6	-	0.496	-

TO-247 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.06	0.0772	0.0812
b2	2.96	3.06	0.117	0.121
c	0.59	0.66	0.0232	0.0260
D	20.90	21.10	0.8235	0.8313
D1	16.25	16.85	0.6403	0.6639
E	15.70	15.90	0.6186	0.6265
E1	13.10	13.50	0.5161	0.5319
e	5.44		0.2143	
L	19.80	20.10	0.7801	0.7919
ΦP	3.50	3.70	0.1379	0.1458
ΦP1	0	7.30	0	0.2876

10 Attentions

- Jiangsu Donghai Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Donghai products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2021.6.05	1.0	Original	